

# **DCR1576SY**

# **Phase Control Thyristor**

Replaces January 2000 version, DS4355-4.0

DS4355-5.0 July 2001

# **FEATURES**

- Double Side Cooling
- High Surge Capability
- High Mean Current
- Fatigue Free

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control

### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Voltages V <sub>DRM</sub> V RRM V	Conditions
DCR1576SY52	5200	$T_{ij} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR1576SY50	5000	$I_{DRM}^{y} = I_{RRM} = 500 \text{mA},$
DCR1576SY48	4800	$V_{DRM}$ , $V_{RRM}$ $t_p = 10ms$ ,
DCR1576SY46	4600	V <sub>DSM</sub> & V <sub>RSM</sub> =
DCR1576SY44	4400	V <sub>DRM</sub> & V <sub>RRM</sub> + 100V
DCR1576SY42	4200	Respectively

Lower voltage grades available.

# **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR1575SY36

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

### **KEY PARAMETERS**

 $V_{DRM}$  5200V  $I_{T(AV)}$  2162A  $I_{TSM}$  40000A  $dVdt^*$  1000V/ $\mu s$  dI/dt 300A/ $\mu s$ 

<sup>\*</sup>Higher dV/dt selections available

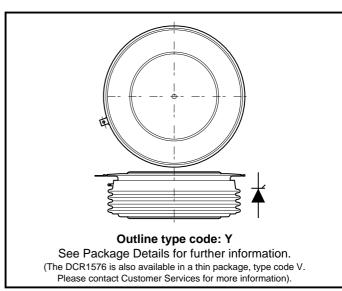


Fig. 1 Package outline



# **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units	
Double Sid	e Cooled				
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	2162	Α	
I <sub>T(RMS)</sub>	RMS value	-	3396	А	
I <sub>T</sub>	Continuous (direct) on-state current	-	3200	А	
Single Side Cooled (Anode side)					
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1440	Α	
I <sub>T(RMS)</sub>	RMS value	-	2261	Α	
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	1984	Α	

# **CURRENT RATINGS**

 $T_{case} = 80^{\circ}C$  unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sic	Double Side Cooled						
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1720	Α			
I <sub>T(RMS)</sub>	RMS value	-	2700	Α			
I <sub>T</sub>	Continuous (direct) on-state current	-	2500	А			
Single Side Cooled (Anode side)							
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	1120	А			
I <sub>T(RMS)</sub>	RMS value	-	1760	А			
I <sub>T</sub>	Continuous (direct) on-state current	-	1510	А			



# **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine; T <sub>case</sub> = 125°C	32.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	V <sub>R</sub> = 50% V <sub>RRM</sub> - 1/4 sine	5.12 x 10 <sup>6</sup>	A²s
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine; T <sub>case</sub> = 125°C	40.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	8.0 x 10 <sup>6</sup>	A²s

# THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.0095	°C/W
		Single side cooled	Anode dc	-	0.019	°C/W
			Cathode dc	-	0.019	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Clamping force 50.0kN with mounting compound	Double side	-	0.002	°C/W
			Single side	-	0.004	°C/W
T <sub>vj</sub>	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	150	°C
-	Clamping force			45.0	55.0	kN



# **DYNAMIC CHARACTERISTICS**

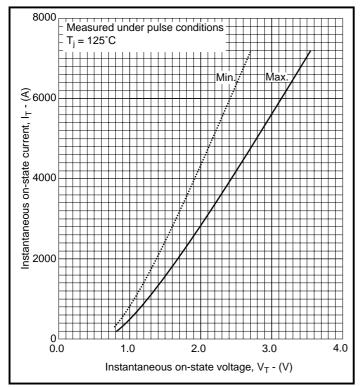
Symbol	Parameter	Conditions		Тур.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> T <sub>j</sub> = 125°C.		•	1000	V/μs
all /alk	Data of vice of an atom comment	ise of on-state current Gate source 20V, 20Ω (AV)	Repetitive 50Hz	-	150	A/μs
dl/dt	Rate of rise of on-state current		Non-repetitive	-	300	A/μs
V <sub>T(TO)</sub>	Threshold voltage	At T <sub>vj</sub> = 125°C		-	1.05	V
r <sub>T</sub>	On-state slope resistance	At T <sub>vj</sub> = 125°C		-	0.34	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , Gate source 30V, 15 $\Omega$ Rise time 0.5 $\mu$ s, $T_j = 25^{\circ}$ C		-	2.5	μs
I <sub>L</sub>	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 5V$		550	1000	mA
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{g-k} = \infty$		150	300	mA
t <sub>q</sub>	Turn-off time	$\begin{split} &I_{T} = 800\text{A, } t_{p} = 1\text{ms, } T_{j} = 125^{\circ}\text{C,} \\ &V_{RM} = 50\text{V, } dI_{RR}/dt = 20\text{A}/\mu\text{s,} \\ &V_{DR} = 67\% \ V_{DRM}, \ dV_{DR}/dt = 20\text{V}/\mu\text{s linear} \end{split}$		1.0	-	ms

# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$	3.0	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 5V$ , $T_{case} = 25^{\circ}C$	300	mA
$V_{\sf GD}$	Gate non-trigger voltage	At V <sub>DRM</sub> T <sub>case</sub> = 125°C	0.25	V
$V_{FGM}$	Peak forward gate voltage	Anode positive with respect to cathode	30	V
$V_{FGN}$	Peak forward gate voltage	Anode negative with respect to cathode	0.25	٧
$V_{RGM}$	Peak reverse gate voltage		5	V
I <sub>FGM</sub>	Peak forward gate current	Anode positive with respect to cathode	30	А
P <sub>GM</sub>	Peak gate power	See table, fig.4	150	W
$P_{G(AV)}$	Mean gate power		10	W



# **CURVES**



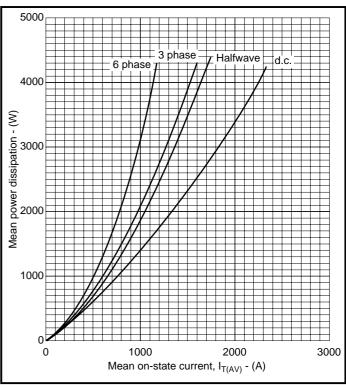


Fig.2 Maximum (limit) on-state characteristics

Fig.3 Dissipation curves

 $V_{TM}$  Equation:-

 $V_{TM} = A + BIn (I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.6963535

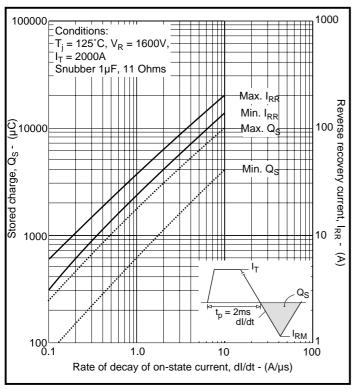
B = 0.1224886

 $C = 3.3104885 \times 10^{-4}$ 

 $D = 1.619778 \times 10^{-4}$ 

these values are valid for  $T_i = 125^{\circ}C$  for  $I_T 500A$  to 7200A





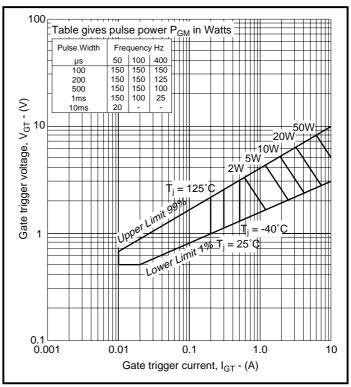


Fig.4 Stored charge

Fig.5 Gate characteristics

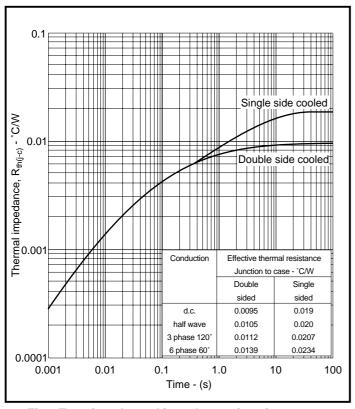


Fig.6 Transient thermal impedance - junction to case

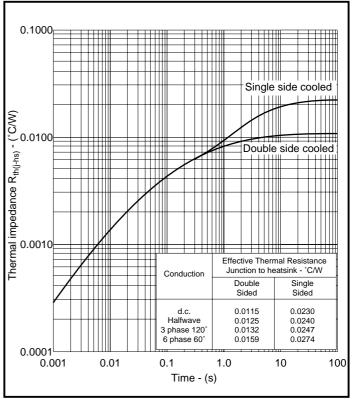


Fig.7 Transient thermal impedance - junction to heatsink



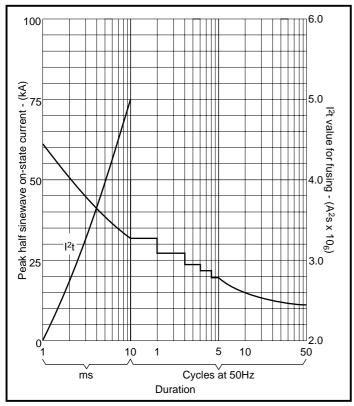
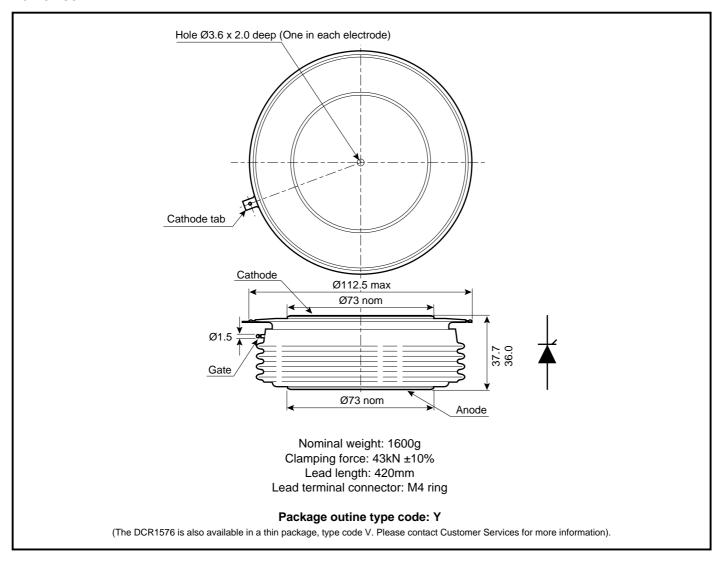


Fig.7 Surge (non-repetitive) on-state current vs time (with 50%  $\rm V_{RRM}$  at  $\rm T_{case}$  = 125°C)



# **PACKAGE DETAILS**

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





### **POWER ASSEMBLY CAPABILITY**

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

#### **DEVICE CLAMPS**

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

#### **HEATSINKS**

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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